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(71) 申请人(对除美国以外的所有指定国): 深圳市朗科科技有限公司(NETAC TECHNOLOGY CO., LTD.) [CN/CN]; 中国广东省深圳市南山区高新南一道中国科技开发院孵化大楼六楼, Guangdong 518057 (CN).
(72) 发明人;及
(75) 发明人/申请人(仅对美国): 熊国平(XIONG, Guoping) [CN/CN]; 中国广东省深圳市南山区高新南一道中国科技开发院孵化大楼六楼, Guangdong 518057 (CN).
(74) 代理人: 北京纪凯知识产权代理有限公司(JEEKAI & PARTNERS); 中国北京市西城区宣武门西大街甲129号, Beijing 100031 (CN).

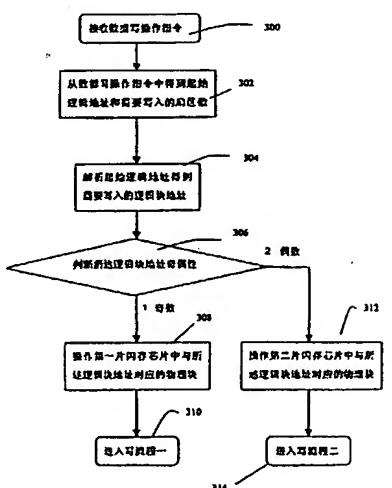
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(54) Title: DATA WRITE-IN METHOD FOR FLASH MEMORY

(54) 发明名称: 闪存介质数据写入方法



300 RECEIVE THE DATA WRITE-IN OPERATING INSTRUCTION
302 OBTAIN THE START LOGICAL ADDRESS AND THE NUMBER OF THE SECTOR THAT SHOULD BE WROTE-IN ACCORDING TO THE DATA WRITE-IN OPERATING INSTRUCTION
304 ANALYSE THE START LOGICAL ADDRESS TO OBTAIN THE LOGICAL ADDRESS THAT SHOULD BE WROTE-IN
306 JUDGE THE PARITY OF SAID LOGICAL BLOCK ADDRESS
308 OPERATE ON THE PHYSICAL BLOCK WHICH CORRESPONDING TO SAID LOGICAL BLOCK ADDRESS AND IN THE FIRST FLASH CHIP
310 GO TO THE WRITING PROCESS ONE
312 OPERATE ON THE PHYSICAL BLOCK WHICH CORRESPONDING TO SAID LOGICAL BLOCK ADDRESS AND IN THE SECOND FLASH CHIP
314 GO TO THE WRITING PROCESS TWO
1 ODD
2 EVEN

(57) Abstract: The present invention provide a data write-in method of flash memory for writing data into two or more flash chips, the method comprise: priority corresponds the physical blocks in the two flash chips to the odd logical block address and the even logical block address respectively; analyse the logical block address which corresponds to the write-in operation from the data write-in instruction; judge the parity of said logical block address and select the corresponding flash chip according to the result; operate the flash chip, detect whether or not the other flash chip needs to be programmed or erased after direct the instruction to program or erase the flash chip, when the other flash chip needs to be programmed or erased, then direct the program or erase instruction to the other flash chip. Using the method of the present invention can program and erase two flash chips simultaneously, thereby increase the data write-in speed greatly.